

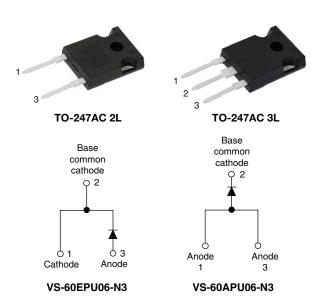
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Vishay Semiconductors

COMPLIANT

HALOGEN FREE

Ultrafast Soft Recovery Diode, 60 A FRED Pt®



PRIMARY CHARACTERISTICS				
I _{F(AV)}	60 A			
V_{R}	600 V			
V _F at I _F	1.11 V			
t _{rr} typ.	See Recovery table			
T _J max.	175 °C			
Package	TO-247AC 2L, TO-247AC 3L			
Circuit configuration	Single			

FEATURES

- · Ultrafast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Designed and qualified according to JEDEC®-JESD 47



BENEFITS

- · Reduced RFI and EMI
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION / APPLICATIONS

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems.

The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for HF welding, power converters and other applications where switching losses are not significant portion of the total losses.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V_R		600	V	
Continuous forward current	I _{F(AV)}	T _C = 116 °C	60		
Single pulse forward current	I _{FSM}	$T_{C} = 25 ^{\circ}\text{C}, t_{p} = 10 \text{ms}$	600	Α	
Maximum repetitive forward current	I _{FRM}	Square wave, 20 kHz	120		
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-		
Forward voltage	V_{F}	I _F = 60 A	-	1.35	1.68	V	
		I _F = 60 A, T _J = 125 °C	-	1.20	1.42		
		I _F = 60 A, T _J = 175 °C	-	1.11	1.30		
Reverse leakage current	_	$V_R = V_R$ rated	-	-	50		
	I _R	$T_J = 150 ^{\circ}\text{C}$, $V_R = V_R$ rated	-	-	500	μA	
Junction capacitance	C _T	V _R = 600 V	-	39	-	pF	



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A, di}_F/\text{dt} = 200 \text{ A/}\mu\text{s, V}_R = 30 \text{ V}$		-	34	45	
Reverse recovery time	t _{rr}	T _J = 25 °C	I _F = 60 A di _F /dt = 200 A/μs V _R = 200 V	-	81	-	ns A
		T _J = 125 °C		-	164	-	
Peak recovery current I _R	I _{RRM}	T _J = 25 °C		-	7.4	-	
		T _J = 125 °C		- 17.0	17.0	-	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		=	300	-	nC
		T _J = 125 °C		-	1394	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction to case	R _{thJC}		-	-	0.63	K/W
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	40	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.2	-	K/W
Weight			-	5.5	-	g
vveignt			-	0.2	-	oz.
May ating to you			1.2	-	2.4	N · m
Mounting torque			10	-	20	lbf ⋅ in
Madin de la		Case style TO-247AC 2L	60EPU06			
Marking device		Case style TO-247AC 3L	60APU06			

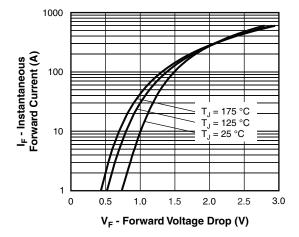


Fig. 1 - Typical Forward Voltage Drop Characteristics

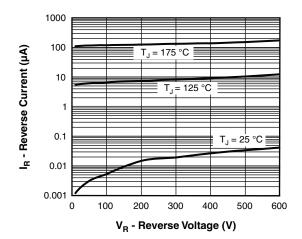


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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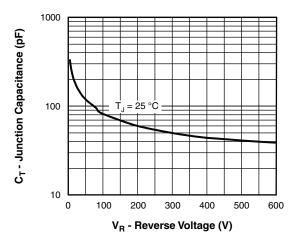


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

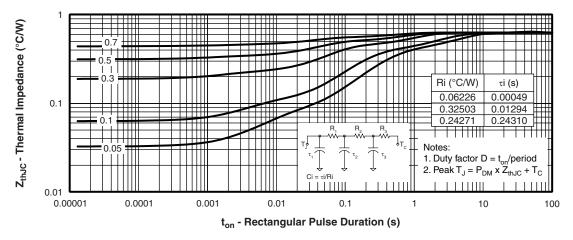


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

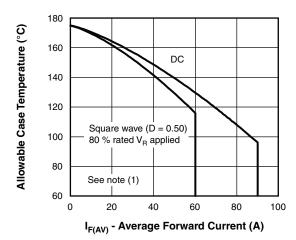


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

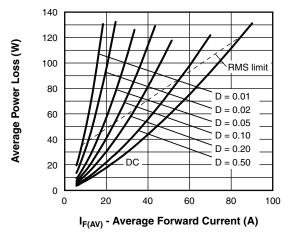


Fig. 6 - Forward Power Loss Characteristics

Note

Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{th,JC}; Pd = forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 6); Pd_{REV} = inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = 80 % rated V_R

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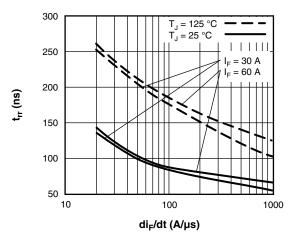


Fig. 7 - Typical Reverse Recovery Time vs. di_F/dt

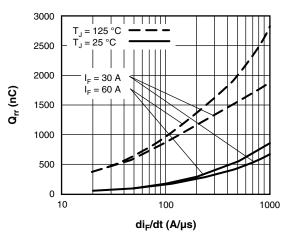
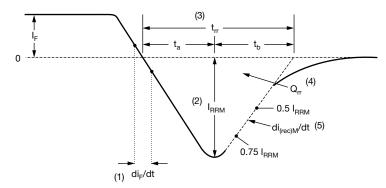


Fig. 8 - Typical Stored Charge vs. di_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_F$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

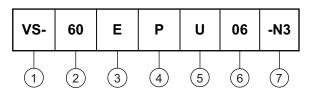
Fig. 9 - Reverse Recovery Waveform and Definitions

VS-60EPU06-N3, VS-60APU06-N3

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (60 = 60 A)

3 - Circuit configuration:

• E = single diode, 2 pins

• A = single diode, 3 pins

4 - Package:

P = TO-247AC

5 - Type of silicon:

U = ultrafast recovery

6 - Voltage rating (06 = 600 V)

7 - Environmental digit:

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)				
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION	
VS-60EPU06-N3	25	500	Antistatic plastic tube	
VS-60APU06-N3	25	500	Antistatic plastic tube	

LINKS TO RELATED DOCUMENTS			
Dimensions	TO-247AC 2L	www.vishay.com/doc?96144	
Dimensions	TO-247AC 3L	www.vishay.com/doc?96138	
Dark madina information	TO-247AC 2L	www.vishay.com/doc?95648	
Part marking information	TO-247AC 3L	www.vishay.com/doc?95007	



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